



DONGGUAN NANJING ELECTRONICS LTD.,

TO-92 Plastic-Encapsulate Transistors

A92 TRANSISTOR (PNP)

FEATURES

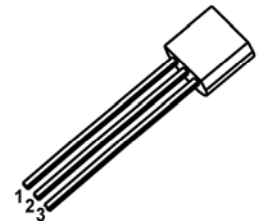
- High voltage

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-300	V
V _{CE0}	Collector-Emitter Voltage	-300	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-200	mA
I _{CM}	Collector Current -Pulsed	-500	mA
P _C	Collector Power Dissipation	625	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/mW
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/mW

TO-92

- 1.EMITTER
- 2.BASE
- 3.COLLECTOR



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-300			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-300			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} = -200 V, I _E =0			-0.25	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5 V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} = -10 V, I _C = -1 mA	60			
	h _{FE(2)}	V _{CE} = -10V, I _C = -10 mA	80		250	
	h _{FE(3)}	V _{CE} = -10 V, I _C = -80 mA	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -20 mA, I _B = -2 mA			-0.2	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -20 mA, I _B = -2 mA			-0.9	V
Transition frequency	f _T	V _{CE} = -20 V, I _C = -10 mA f = 30MHz	50			MHz

CLASSIFICATION OF h_{FE(2)}

Rank	A	B ₁	B ₂	C
Range	80-100	100-150	150-200	200-250